

Yin Tang Yang

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2272489/publications.pdf>

Version: 2024-02-01

219
papers

3,004
citations

201575

27
h-index

276775

41
g-index

220
all docs

220
docs citations

220
times ranked

2042
citing authors

#	ARTICLE	IF	CITATIONS
1	Lightweight RFID Protocol for Medical Privacy Protection in IoT. IEEE Transactions on Industrial Informatics, 2018, 14, 1656-1665.	7.2	135
2	Blockchain-based efficient privacy preserving and data sharing scheme of content-centric network in 5G. IET Communications, 2018, 12, 527-532.	1.5	120
3	A Secure and Verifiable Data Sharing Scheme Based on Blockchain in Vehicular Social Networks. IEEE Transactions on Vehicular Technology, 2020, 69, 5826-5835.	3.9	96
4	New Superjunction LDMOS Breaking Silicon Limit by Electric Field Modulation of Buffered Step Doping. IEEE Electron Device Letters, 2015, 36, 47-49.	2.2	69
5	Anonymous and Privacy-Preserving Federated Learning With Industrial Big Data. IEEE Transactions on Industrial Informatics, 2021, 17, 6314-6323.	7.2	69
6	New Superjunction LDMOS With N^+N^- -Type Charges' Compensation Layer. IEEE Electron Device Letters, 2009, 30, 305-307.	2.2	62
7	A Secure and Verifiable Outsourced Access Control Scheme in Fog-Cloud Computing. Sensors, 2017, 17, 1695.	2.1	58
8	Electrical Modeling and Characterization of Shield Differential Through-Silicon Vias. IEEE Transactions on Electron Devices, 2015, 62, 1544-1552.	1.6	52
9	Blockchain-Based Secure Time Protection Scheme in IoT. IEEE Internet of Things Journal, 2019, 6, 4671-4679.	5.5	51
10	Ultra-Compact TSV-Based L-C Low-Pass Filter With Stopband Up to 40 GHz for Microwave Application. IEEE Transactions on Microwave Theory and Techniques, 2019, 67, 738-745.	2.9	49
11	Folded-Accumulation LDMOST: New Power MOS Transistor With Very Low Specific On-Resistance. IEEE Electron Device Letters, 2009, 30, 1329-1331.	2.2	44
12	A Bistable Threshold Accelerometer With Fully Compliant Clamped-Clamped Mechanism. IEEE Sensors Journal, 2010, 10, 1019-1024.	2.4	42
13	Low Specific on-Resistance Power MOS Transistor With Multilayer Carrier Accumulation Breaks the Limit Line of Silicon. IEEE Transactions on Electron Devices, 2011, 58, 2057-2060.	1.6	42
14	An Effective Approach of Reducing the Keep-Out-Zone Induced by Coaxial Through-Silicon-Via. IEEE Transactions on Electron Devices, 2014, 61, 2928-2934.	1.6	40
15	A Collaborative Auditing Blockchain for Trustworthy Data Integrity in Cloud Storage System. IEEE Access, 2020, 8, 94780-94794.	2.6	40
16	Complete 3D-Reduced Surface Field Superjunction Lateral Double-Diffused MOSFET Breaking Silicon Limit. IEEE Electron Device Letters, 2015, 36, 1348-1350.	2.2	38
17	A Compact Microstrip Phase Shifter Employing Reconfigurable Defected Microstrip Structure (RDMS) for Phased Array Antennas. IEEE Transactions on Antennas and Propagation, 2015, 63, 1985-1996.	3.1	36
18	Wideband Substrate Integrated Waveguide Bandpass Filter Based on 3-D ICs. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2019, 9, 728-735.	1.4	36

#	ARTICLE	IF	CITATIONS
19	An ultra-lightweight RFID authentication scheme for mobile commerce. Peer-to-Peer Networking and Applications, 2017, 10, 368-376.	2.6	35
20	Two Novel C3N4 Phases: Structural, Mechanical and Electronic Properties. Materials, 2016, 9, 427.	1.3	34
21	Compact Bandpass Filter and Diplexer With Wide-Stopband Suppression Based on Balanced Substrate-Integrated Waveguide. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 54-64.	2.9	33
22	Theoretical investigations of group IV alloys in the Lonsdaleite phase. Journal of Materials Science, 2018, 53, 2785-2801.	1.7	31
23	Particle Swarm Optimization Algorithm-Based Design Method for Ultrasonic Transducers. Micromachines, 2020, 11, 715.	1.4	31
24	Penta-C20: A Superhard Direct Band Gap Carbon Allotrope Composed of Carbon Pentagon. Materials, 2020, 13, 1926.	1.3	31
25	Multi-layer polymer-metal structures for acoustic impedance matching in high-frequency broadband ultrasonic transducers design. Applied Acoustics, 2020, 160, 107123.	1.7	30
26	Contactless microparticle control via ultrahigh frequency needle type single beam acoustic tweezers. Applied Physics Letters, 2016, 109, 173509.	1.5	29
27	A 1.4-mW 10-Bit 150-MS/s SAR ADC With Nonbinary Split Capacitive DAC in 65-nm CMOS. IEEE Transactions on Circuits and Systems II: Express Briefs, 2018, 65, 1524-1528.	2.2	29
28	0.36BiScO3-0.64PbTiO3 piezoelectric ceramics for high temperature ultrasonic transducer applications. Journal of Alloys and Compounds, 2018, 743, 365-371.	2.8	28
29	A 1.2-V 2.41-GHz Three-Stage CMOS OTA With Efficient Frequency Compensation Technique. IEEE Transactions on Circuits and Systems I: Regular Papers, 2019, 66, 20-30.	3.5	28
30	An optimization design strategy of 1 μ m ³ piezocomposite ultrasonic transducer for imaging applications. Materials Today Communications, 2020, 24, 100991.	0.9	28
31	New Superjunction LDMOS With the Complete Charge Compensation by the Electric Field Modulation. IEEE Electron Device Letters, 2014, 35, 1115-1117.	2.2	27
32	Novel LDMOS Optimizing Lateral and Vertical Electric Field to Improve Breakdown Voltage by Multi-Ring Technology. IEEE Electron Device Letters, 2018, 39, 1358-1361.	2.2	27
33	An Efficient Multi-Message and Multi-Receiver Signcryption Scheme for Heterogeneous Smart Mobile IoT. IEEE Access, 2019, 7, 180205-180217.	2.6	27
34	A 4.6-ppm/ $\text{Å}^\circ\text{C}$ High-Order Curvature Compensated Bandgap Reference for BMIC. IEEE Transactions on Circuits and Systems II: Express Briefs, 2019, 66, 1492-1496.	2.2	27
35	Si96: A New Silicon Allotrope with Interesting Physical Properties. Materials, 2016, 9, 284.	1.3	26
36	Theoretical investigations of Ge _{1-x} Sn _x alloys (x=0, 0.333, 0.667, 1) in P42/ncm phase. Journal of Materials Science, 2018, 53, 9611-9626.	1.7	26

#	ARTICLE	IF	CITATIONS
37	Performance Analysis for Relay-Aided Multihop BPPM FSO Communication System Over Exponentiated Weibull Fading Channels With Pointing Error Impairments. <i>IEEE Photonics Journal</i> , 2015, 7, 1-20.	1.0	23
38	Electrical Modeling and Analysis of Differential Dielectric-Cavity Through-Silicon via Array. <i>IEEE Microwave and Wireless Components Letters</i> , 2017, 27, 618-620.	2.0	23
39	Secure, efficient and revocable data sharing scheme for vehicular fogs. <i>Peer-to-Peer Networking and Applications</i> , 2018, 11, 766-777.	2.6	23
40	Novel Superjunction LDMOS With a High- κ Dielectric Trench by TCAD Simulation Study. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 2327-2332.	1.6	23
41	Cloud-based RFID mutual authentication scheme for efficient privacy preserving in IoV. <i>Journal of the Franklin Institute</i> , 2021, 358, 193-209.	1.9	23
42	Novel SiC/Si Heterojunction Power MOSFET With Breakdown Point Transfer Terminal Technology by TCAD Simulation Study. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 3388-3393.	1.6	22
43	A 10-Bit 600-MS/s Time-Interleaved SAR ADC With Interpolation-Based Timing Skew Calibration. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2019, 66, 16-20.	2.2	22
44	Breakdown voltage analysis for the new RESURF AlGaN/GaN HEMTs. <i>Science China Information Sciences</i> , 2012, 55, 473-479.	2.7	21
45	Fabrication of PMN-PT/Epoxy 2^{nd} Composite Ultrasonic Transducers and Analysis Based on Equivalent Circuit Model. <i>Journal of Electronic Materials</i> , 2018, 47, 6842-6847.	1.0	21
46	Analysis of temperature-dependent characteristics of a 4H-SiC metal-semiconductor-metal ultraviolet photodetector. <i>Science Bulletin</i> , 2012, 57, 4427-4433.	1.7	20
47	TAONoC: A Regular Passive Optical Network-on-Chip Architecture Based on Comb Switches. <i>IEEE Transactions on Very Large Scale Integration (VLSI) Systems</i> , 2019, 27, 954-963.	2.1	20
48	Fabrication and Characterization of High-Sensitivity Ultrasonic Transducers With Functionally Graded Design. <i>IEEE Sensors Journal</i> , 2019, 19, 6650-6654.	2.4	20
49	Liquid lens with adjustable focus for ultrasonic imaging. <i>Applied Acoustics</i> , 2021, 175, 107787.	1.7	20
50	Security Analysis of the Kerberos Protocol Using BAN Logic. , 2009, , .		19
51	The Mechanical and Electronic Properties of Carbon-Rich Silicon Carbide. <i>Materials</i> , 2016, 9, 333.	1.3	19
52	Theoretical Analyses of Complete 3-D Reduced Surface Field LDMOS With Folded-Substrate Breaking Limit of Superjunction LDMOS. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 4865-4872.	1.6	19
53	A Superjunction U-MOSFET With SIPOS Pillar Breaking Superjunction Silicon Limit by TCAD Simulation Study. <i>IEEE Electron Device Letters</i> , 2017, 38, 794-797.	2.2	19
54	Wideband Fourth-Harmonic Mixer Operated at 325-500 GHz. <i>IEEE Microwave and Wireless Components Letters</i> , 2018, 28, 242-244.	2.0	19

#	ARTICLE	IF	CITATIONS
55	New Super-Junction LDMOS Breaking Silicon Limit by Multi-Ring Assisted Depletion Substrate. IEEE Transactions on Electron Devices, 2019, 66, 4836-4841.	1.6	19
56	An Effective Approach for Thermal Performance Analysis of 3-D Integrated Circuits With Through-Silicon Vias. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2019, 9, 877-887.	1.4	19
57	Analysis of the novel Snapback-Free LIGBT with fast-switching and improved latch-up immunity by TCAD Simulation. IEEE Electron Device Letters, 2018, , 1-1.	2.2	18
58	Novel Snapback-Free SOI LIGBT With Shorted Anode and Trench Barriers. IEEE Transactions on Electron Devices, 2021, 68, 2408-2413.	1.6	18
59	High frequency needle ultrasonic transducers based on Mn doped piezoelectric single crystal. Journal of Alloys and Compounds, 2020, 832, 154951.	2.8	17
60	Experimental Results for AlGaN/GaN HEMTs Improving Breakdown Voltage and Output Current by Electric Field Modulation. IEEE Transactions on Electron Devices, 2021, 68, 2240-2245.	1.6	17
61	New Al _{0.25} Ga _{0.75} N/GaN HEMTs structure with the partial silicon doping. Micro and Nano Letters, 2012, 7, 9.	0.6	16
62	Low-Loss Air-Cavity Through-Silicon Vias (TSVs) for High Speed Three-Dimensional Integrated Circuits (3-D ICs). IEEE Microwave and Wireless Components Letters, 2016, 26, 89-91.	2.0	16
63	SiC/Si heterojunction VDMOS breaking silicon limit by breakdown point transfer technology. Micro and Nano Letters, 2018, 13, 96-99.	0.6	16
64	Novel Lateral Double-Diffused MOSFET With Ultralow On-Resistance by the Variable Resistivity of Drift Region. IEEE Electron Device Letters, 2020, 41, 1681-1684.	2.2	16
65	Performance Analysis of Multihop Parallel Free-Space Optical Systems Over Exponentiated Weibull Fading Channels. IEEE Photonics Journal, 2015, 7, 1-17.	1.0	15
66	Wideband Electromagnetic Model and Analysis of Shielded-Pair Through-Silicon Vias. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2018, 8, 473-481.	1.4	15
67	Analysis of the Fast-Switching LIGBT With Double Gates and Integrated Schottky Barrier Diode. IEEE Transactions on Electron Devices, 2019, 66, 2675-2680.	1.6	15
68	Recent Development and Perspectives of Optimization Design Methods for Piezoelectric Ultrasonic Transducers. Micromachines, 2021, 12, 779.	1.4	15
69	Focus of ultrasonic underwater sound with 3D printed phononic crystal. Applied Physics Letters, 2021, 119, .	1.5	15
70	The forbidden band and size selectivity of acoustic radiation force trapping. IScience, 2021, 24, 101988.	1.9	15
71	A new RFID ultra-lightweight authentication protocol for medical privacy protection in smart living. Computer Communications, 2022, 186, 121-132.	3.1	15
72	Multihop FSO Over Exponentiated Weibull Fading Channels With Nonzero Boresight Pointing Errors. IEEE Photonics Technology Letters, 2016, 28, 1747-1750.	1.3	14

#	ARTICLE	IF	CITATIONS
73	Monte Carlo Investigation of High-Field Electron Transport Characteristics in ZnMgO/ZnO Heterostructures. IEEE Transactions on Electron Devices, 2016, 63, 517-523.	1.6	14
74	A Novel Silicon Allotrope in the Monoclinic Phase. Materials, 2017, 10, 441.	1.3	14
75	Permutation Matrix Encryption Based Ultralightweight Secure RFID Scheme in Internet of Vehicles. Sensors, 2019, 19, 152.	2.1	14
76	Negative differential resistance in single-walled SiC nanotubes. Science Bulletin, 2008, 53, 3770-3772.	1.7	13
77	Efficient ID-based registration protocol featured with user anonymity in mobile IP networks. IEEE Transactions on Wireless Communications, 2010, 9, 594-604.	6.1	13
78	A Development Summarization of the Power Semiconductor Devices. IETE Technical Review (Institution) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 3	2.1	13
79	Analytical model of LDMOS with a double step buried oxide layer. Solid-State Electronics, 2016, 123, 6-14.	0.8	13
80	Enhancement-mode AlGaN/GaN HEMTs with optimised electric field using a partial GaN cap layer. Micro and Nano Letters, 2017, 12, 763-766.	0.6	13
81	Theory Analyses of SJ-LDMOS With Multiple Floating Buried Layers Based on Bulk Electric Field Modulation. IEEE Transactions on Electron Devices, 2018, 65, 2565-2572.	1.6	13
82	Secure ultra-lightweight RFID mutual authentication protocol based on transparent computing for IoT. Peer-to-Peer Networking and Applications, 2018, 11, 723-734.	2.6	13
83	Accurate Inductance Modeling of 3-D Inductor Based on TSV. IEEE Microwave and Wireless Components Letters, 2018, 28, 900-902.	2.0	13
84	Breakdown Mechanisms of Power Semiconductor Devices. IETE Technical Review (Institution of) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 3	2.1	13
85	Optimization Design of Ultrasonic Transducer With Multimatching Layer. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2021, 68, 2202-2211.	1.7	13
86	Structural, Mechanical, Anisotropic, and Thermal Properties of AIAs in oC12 and hP6 Phases under Pressure. Materials, 2018, 11, 740.	1.3	12
87	Novel Si/SiC Heterojunction Lateral Double-Diffused Metal Oxide Semiconductor With SIPOS Field Plate by Simulation Study. IEEE Journal of the Electron Devices Society, 2021, 9, 114-120.	1.2	12
88	Study of Self-Heating and High-Power Microwave Effects for Enhancement-Mode p-Gate GaN HEMT. Micromachines, 2022, 13, 106.	1.4	12
89	A Survey on Analog-to-Digital Converter Integrated Circuits for Miniaturized High Resolution Ultrasonic Imaging System. Micromachines, 2022, 13, 114.	1.4	12
90	Elastic anisotropy and electronic properties of Si3N4 under pressures. AIP Advances, 2016, 6, .	0.6	11

#	ARTICLE	IF	CITATIONS
91	Novel LDMOS with assisted deplete-substrate layer consist of super junction under the drain. , 2017, , .		11
92	A Handheld Nano Through-Wall Radar Locating With the Gain-Enhanced Vivaldi Antenna. IEEE Sensors Journal, 2020, 20, 4420-4429.	2.4	11
93	First-Principles Study on Structural, Mechanical, Anisotropic, Electronic and Thermal Properties of III-Phosphides: XP (X = Al, Ga, or In) in the P6422 Phase. Materials, 2020, 13, 686.	1.3	11
94	Multilayer Stairstep Piezoelectric Structure Design for Ultrabroad-Bandwidth Ultrasonic Transducer. IEEE Sensors Journal, 2021, 21, 19889-19895.	2.4	11
95	A Miniatured Passive Low-Pass Filter With Ultrawide Stopband Based on 3-D Integration Technology. IEEE Microwave and Wireless Components Letters, 2022, 32, 29-32.	2.0	11
96	A Review of UltraHigh Frequency Ultrasonic Transducers. Frontiers in Materials, 2022, 8, .	1.2	11
97	Memory-Efficient Deformable Convolution Based Joint Denoising and Demosaicing for UHD Images. IEEE Transactions on Circuits and Systems for Video Technology, 2022, 32, 7346-7358.	5.6	11
98	Average bit error rate performance analysis of subcarrier intensity modulated MRC and EGC FSO systems with dual branches over M distribution turbulence channels. Optoelectronics Letters, 2015, 11, 281-285.	0.4	10
99	A New Phase of GaN. Journal of Chemistry, 2016, 2016, 1-9.	0.9	10
100	A 140â€“220-GHz Balanced Doubler With 8.7%â€“12.7% Efficiency. IEEE Microwave and Wireless Components Letters, 2018, 28, 515-517.	2.0	10
101	Nonlinear Electrothermal Model for Investigating Transient Temperature Responses of a Through-Silicon Via Array Applied With Gaussian Pulses in 3-D IC. IEEE Transactions on Electron Devices, 2019, 66, 1032-1040.	1.6	10
102	An Efficient Optimization Design for 1 MHz Ultrasonic Transmitting Transducer. IEEE Sensors Journal, 2021, 21, 7420-7427.	2.4	10
103	DnRCNN: Deep Recurrent Convolutional Neural Network for HSI Destriping. IEEE Transactions on Neural Networks and Learning Systems, 2023, 34, 3255-3268.	7.2	10
104	First-principles study on mechanical and elastic properties of B<i>x</i>Al<i>1-x</i>P alloys. AIP Advances, 2017, 7, .	0.6	9
105	Thermal-Aware Modeling and Analysis for a Power Distribution Network Including Through-Silicon-Vias in 3-D ICs. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2019, 38, 1278-1290.	1.9	9
106	Fast-Switching Lateral IGBT with Trench/Planar Gate and Integrated Schottky Barrier Diode (SBD). , 2019, , .		9
107	Mechanism of AlGaAs/InGaAs pHEMT Nonlinear Response Under High-Power Microwave Radiation. IEEE Journal of the Electron Devices Society, 2020, 8, 731-737.	1.2	9
108	A 1V 3.5 Î¼W Bio-AFE With Chopper-Capacitor-Chopper Integrator-Based DSL and Low Power GM-C Filter. IEEE Transactions on Circuits and Systems II: Express Briefs, 2022, 69, 5-9.	2.2	9

#	ARTICLE	IF	CITATIONS
109	Effects of Internal Gain and Illumination-Induced Stored Charges in MgZnO Metal-Semiconductor-Metal Photodetectors. IEEE Transactions on Electron Devices, 2016, 63, 1600-1607.	1.6	8
110	High Resolution ADC for Ultrasound Color Doppler Imaging Based on MASH Sigma-Delta Modulator. IEEE Transactions on Biomedical Engineering, 2020, 67, 1438-1449.	2.5	8
111	Accumulation-Mode Device: New Power MOSFET Breaking Superjunction Silicon Limit by Simulation Study. IEEE Transactions on Electron Devices, 2020, 67, 1085-1089.	1.6	8
112	Intelligent Optimization of Matching Layers for Piezoelectric Ultrasonic Transducer. IEEE Sensors Journal, 2021, 21, 13107-13115.	2.4	8
113	Electromechanical modeling of stretchable interconnects. Journal of Computational Electronics, 2017, 16, 202-209.	1.3	7
114	Novel superjunction LDMOS with multi-floating buried layers. , 2017, , .		7
115	Structural, Electronic, and Thermodynamic Properties of Tetragonal $t\text{-SixGe}_{3-x}\text{N}_4$. Materials, 2018, 11, 397.	1.3	7
116	Si/SiC heterojunction lateral double-diffused metal oxide semiconductor field effect transistor with breakdown point transfer (BPT) terminal technology. Micro and Nano Letters, 2019, 14, 1092-1095.	0.6	7
117	An Efficient Optimization Design of Liquid Lens for Acoustic Pattern Control. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2021, 68, 1546-1554.	1.7	7
118	High-Frequency $0.36\text{BiScO}_3\text{-}0.64\text{PbTiO}_3$ Ultrasonic Transducer for High-Temperature Imaging Application. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2022, 69, 761-768.	1.7	7
119	Monte Carlo analysis of transient electron transport in wurtzite $\text{Zn}_{1-x}\text{Mg}_x\text{O}$ combined with first principles calculations. AIP Advances, 2015, 5, .	0.6	6
120	Modeling and understanding of the frequency dependent HPM upset susceptibility of the CMOS inverter. Science China Information Sciences, 2015, 58, 1-11.	2.7	6
121	Analytical model of LDMOS with a single step buried oxide layer. Superlattices and Microstructures, 2016, 97, 358-370.	1.4	6
122	Proxy-assisted access control scheme of cloud data for smart cities. Personal and Ubiquitous Computing, 2017, 21, 937-947.	1.9	6
123	SRNoC: An Ultra-Fast Configurable FPGA-Based NoC Simulator Using Switch-Router Architecture. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2020, 39, 2798-2811.	1.9	6
124	Unified Analytical Model for SOI LDMOS With Electric Field Modulation. IEEE Journal of the Electron Devices Society, 2020, 8, 686-694.	1.2	6
125	Acoustic Hole-Hologram for Ultrasonic Focusing With High Sensitivity. IEEE Sensors Journal, 2021, 21, 8935-8942.	2.4	6
126	Compact and Physics-Based Modeling of 3-D Inductor Based on Through Silicon Via. IEEE Electron Device Letters, 2021, 42, 1559-1562.	2.2	6

#	ARTICLE	IF	CITATIONS
127	An Anisotropic Equivalent Thermal Model for Shield Differential Through-Silicon Vias. <i>Micromachines</i> , 2021, 12, 1223.	1.4	6
128	Ultrawide Bandwidth High-Frequency Ultrasonic Transducers With Gradient Acoustic Impedance Matching Layer for Biomedical Imaging. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , 2022, 69, 1952-1959.	1.7	6
129	Super junction LDMOS with step field oxide layer. <i>Micro and Nano Letters</i> , 2016, 11, 666-669.	0.6	5
130	A Background Timing Skew Calibration Technique in Time-Interleaved ADCs With Second Order Compensation. , 2018, , .		5
131	3D numerical simulations of single-event transient effects in SOI FinFETs. <i>Journal of Computational Electronics</i> , 2018, 17, 1608-1614.	1.3	5
132	EARS-DM: Efficient Auto Correction Retrieval Scheme for Data Management in Edge Computing. <i>Sensors</i> , 2018, 18, 3616.	2.1	5
133	New Strained LDMOS With Ultralow ON-Resistance by Si ¹ and C ^y Source Stressor for About 20 V Low-Voltage Applications. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 4998-5004.	1.6	5
134	Encrypted Data Retrieval and Sharing Scheme in Space-Air-Ground-Integrated Vehicular Networks. <i>IEEE Internet of Things Journal</i> , 2022, 9, 5957-5970.	5.5	5
135	Novel SOI LDMOS Without RESURF Effect by Flexible Substrate for Flexible Electronic Systems. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 4150-4155.	1.6	5
136	Novel Enhance-Mode AlGaIn/GaN JFET With BV of Over 1.2 kV Maintaining Low $R_{ON,sp}$. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 1200-1205.	1.6	5
137	High-Frequency Self-Focusing Ultrasonic Transducer With Piezoelectric Metamaterial. <i>IEEE Electron Device Letters</i> , 2022, 43, 946-949.	2.2	5
138	Dynamics of a novel bistable mechanism with mechanical-magnetic coupled structure. <i>Journal of Central South University</i> , 2012, 19, 1853-1858.	1.2	4
139	Secure and private key management scheme in big data networking. <i>Peer-to-Peer Networking and Applications</i> , 2018, 11, 992-999.	2.6	4
140	Etched Al _{0.32} Ga _{0.68} N/GaN HEMTs with high output current and breakdown voltage (>600 V). <i>Micro and Nano Letters</i> , 2018, 13, 676-679.	0.6	4
141	Analytical model of buried air partial SOI LDMOS. <i>Superlattices and Microstructures</i> , 2019, 132, 106162.	1.4	4
142	Vertical double diffused MOSFET with step HK insulator improving electric field modulation. <i>Micro and Nano Letters</i> , 2019, 14, 219-222.	0.6	4
143	Simulation Study on Dynamic and Static Characteristics of Novel SiC Gate-Controlled Bipolar-Field-Effect Composite Transistor. <i>IEEE Journal of the Electron Devices Society</i> , 2020, 8, 1082-1088.	1.2	4
144	AC-SJ VDMOS with ultra-low resistance. <i>Micro and Nano Letters</i> , 2020, 15, 230-233.	0.6	4

#	ARTICLE	IF	CITATIONS
145	A breakdown model of LDMOS optimizing lateral and vertical electric field to improve breakdown voltage by multi-ring technology. Solid-State Electronics, 2020, 166, 107775.	0.8	4
146	Experimental of Folded Accumulation Lateral Double-diffused Transistor with Low Specific On Resistance. , 2021, , .		4
147	Accumulation-Mode Lateral Double-Diffused MOSFET Breaking Silicon Limit by Eliminating Dependence of Specific ON-Resistance on Doping Concentration. IEEE Transactions on Electron Devices, 2021, 68, 2414-2419.	1.6	4
148	Optimization design of high-frequency ultrasonic transducer based on ANFIS and particle swarm optimization algorithm. Applied Acoustics, 2022, 187, 108507.	1.7	4
149	New Strained Lateral MOSFET With Ultralow On-Resistance by Surrounded Stress Dielectric Layer. IEEE Electron Device Letters, 2022, 43, 525-528.	2.2	4
150	Wide-Stopband Substrate Integrated Waveguide Filter Power Divider Based on Through Glass Quartz Via (TQV) Technology. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2022, 12, 1196-1203.	1.4	4
151	Effect of dummy vias on interconnect temperature variation. Science Bulletin, 2011, 56, 2286-2290.	1.7	3
152	Performance analysis of relay-aided free-space optical communication system over gamma-gamma fading channels with pointing errors. Optoelectronics Letters, 2016, 12, 294-298.	0.4	3
153	Novel lateral double-diffused MOSFET with folded silicon and high-permittivity dielectric breaking silicon limit. Superlattices and Microstructures, 2018, 123, 280-285.	1.4	3
154	Analysis of the novel Si/SiC heterojunction IGBT characteristics by TCAD simulation. Superlattices and Microstructures, 2018, 122, 631-635.	1.4	3
155	Analysis of the Coupling Capacitance Between TSVs and Adjacent RDL Interconnections. IEEE Transactions on Electromagnetic Compatibility, 2019, 61, 512-520.	1.4	3
156	Noise Characteristics of MgZnO-Based Metalâ€“Semiconductorâ€“Metal Photodetector. IEEE Transactions on Electron Devices, 2019, 66, 983-990.	1.6	3
157	Novel Power MOSFET With Partial SiC/Si Heterojunction to Improve Breakdown Voltage by Breakdown Point Transfer (BPT) Terminal Technology. IEEE Journal of the Electron Devices Society, 2020, 8, 559-564.	1.2	3
158	New Strained Silicon-On-Insulator Lateral MOSFET With Ultralow ON-Resistance by Si_{1-x}Ge_x-P-Top Layer and Trench Gate. IEEE Electron Device Letters, 2021, 42, 788-791.	2.2	3
159	Mechanism Analysis and Thermal Damage Prediction of High-Power Microwave Radiated CMOS Circuits. IEEE Transactions on Device and Materials Reliability, 2021, 21, 444-451.	1.5	3
160	Novel Vertical Power MOSFET With Step Hk Insulator Close to Super Junction Limit Relationship Between Breakdown Voltage and Specific ON-Resistance by Improving Electric Field Modulation. IEEE Transactions on Electron Devices, 2021, 68, 5048-5054.	1.6	3
161	Time-Domain Power Distribution Network (PDN) Analysis for 3-D Integrated Circuits Based on WLP-FDTD. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2022, 12, 551-561.	1.4	3
162	Novel Step Floating Islands VDMOS with Low Specific on-Resistance by TCAD Simulation. Micromachines, 2022, 13, 573.	1.4	3

#	ARTICLE	IF	CITATIONS
163	3-D Compact Marchand Balun Design Based on Through-Silicon via Technology for Monolithic and 3-D Integration. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2022, 30, 1107-1118.	2.1	3
164	Frequency Emergency Control Strategy Considering the Operation Speed of Frequency Regulation resources. , 2018, , .		2
165	The Analysis Model of AlGaIn/GaN HEMTs with Electric Field Modulation Effect. IETE Technical Review (Institution of Electronics and Telecommunication Engineers, India), 2020, 37, 553-564.	2.1	2
166	Novel SOI LIGBT with fast switching by the electric field modulation. Micro and Nano Letters, 2020, 15, 155-158.	0.6	2
167	Adjustable Acoustic Field Controlled by Ultrasonic Projector on Ultrasound Application. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2022, 69, 254-260.	1.7	2
168	Novel Low Loss LIGBT With Assisted Depletion N-Region and P-Buried Layer. IEEE Journal of the Electron Devices Society, 2021, 9, 409-414.	1.2	2
169	Research on the leakage current at sidewall of mesa Ge/Si avalanche photodiode. AIP Advances, 2021, 11, 075320.	0.6	2
170	Complete Accumulation Lateral Double-Diffused MOSFET With Low ON-Resistance Applying Floating Buried Layer. IEEE Transactions on Electron Devices, 2022, 69, 658-663.	1.6	2
171	A TSV-Based 3-D Electromagnetic Bandgap Structure on an Interposer for Noise Suppression. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2022, 12, 147-154.	1.4	2
172	Blockchain-based trust management for verifiable time synchronization service in IoT. Peer-to-Peer Networking and Applications, 2022, 15, 1152-1162.	2.6	2
173	Optimization and Analysis of Microchannels Under Complex Power Distribution in 3-D ICs. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2022, 12, 537-543.	1.4	2
174	Matching layer design of a 2D piezo-composite ultrasonic transducer for biomedical imaging. Structural and Multidisciplinary Optimization, 2022, 65, 1.	1.7	2
175	Compact Interdigital Bandpass Filter, Diplexer, and Triplexer Based on Through Quartz Vias (TQVs). IEEE Transactions on Components, Packaging and Manufacturing Technology, 2022, 12, 988-997.	1.4	2
176	Growth and characterization of Si/SiN/SiC structures by APCVD process. , 2008, , .		1
177	Transient response of bipolar transistor under intense electromagnetic pulse on collector. , 2009, , .		1
178	Fast Parallel Computation of Tate Pairing. , 2011, , .		1
179	The fabrication and research Of 4H-Sic Schottky metal-semiconductor-metal ultraviolet photodetectors. , 2012, , .		1
180	New folding lateral double diffused metal oxide semiconductor breaking silicon limit with ultra-low specific on-resistance. Micro and Nano Letters, 2016, 11, 99-101.	0.6	1

#	ARTICLE	IF	CITATIONS
181	First-principles investigations on structural, elastic and mechanical properties of $\text{BN}_x\text{As}_{1-x}$ ternary alloys. International Journal of Modern Physics B, 2018, 32, 1850152.	1.0	1
182	Application of Novel Terminal Technologies for Superjunction Power MOSFETs. IETE Technical Review (Institution of Electronics and Telecommunication Engineers, India), 2018, 35, 402-412.	2.1	1
183	Evaluation of Frequency Regulation Capability of Wind Power Considering its Uncertainty. , 2018, , .		1
184	Electronic and elastic properties of the antiferroelectric structure Mg_2Si under pressure. AIP Conference Proceedings, 2018, , .	0.3	1
185	Wideband Electromagnetic Distribution Characterization and Dielectric Analysis of Shielded-Pair Through-Silicon Via Using Recursive Approximation Algorithm. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2019, 9, 936-944.	1.4	1
186	A Group-Based Laser Power Supply Scheme for Photonic Network on Chip. IEEE Photonics Journal, 2019, 11, 1-14.	1.0	1
187	SiC gate-controlled bipolar field-effect composite transistor with large on-state current. Micro and Nano Letters, 2019, 14, 1406-1409.	0.6	1
188	Thermal Field Analysis for New $\text{AlGaIn}/\text{GaIn}$ HEMT With Partial Etched AlGaIn Layer. IEEE Journal of the Electron Devices Society, 2020, 8, 442-447.	1.2	1
189	A Fast Analysis Method of Multiphysics Coupling for 3-D Microsystem. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2022, 41, 2372-2379.	1.9	1
190	Electrothermal coupling analysis of 3D Integrated Micro System Based on dual cell method. Wuli Xuebao/Acta Physica Sinica, 2021, .	0.2	1
191	Physics based scalable inductance model for three-dimensional solenoid inductors. Microelectronics Journal, 2020, 103, 104867.	1.1	1
192	A 2.5 V, 2.56 ppm/ $^{\circ}\text{C}$ Curvature-Compensated Bandgap Reference for High-Precision Monitoring Applications. Micromachines, 2022, 13, 465.	1.4	1
193	An Optimized Miniaturized Ultrasound Transducer for Transcranial Neuromodulation. Frontiers in Neuroscience, 0, 16, .	1.4	1
194	Novel Si/SiC heterojunction lateral double-diffused metal oxide semiconductor field effect transistor with low specific on-resistance by super junction layer. , 2022, 168, 207298.		1
195	Joint Biological ID : A Secure and Efficient Lightweight Biometric Authentication Scheme. IEEE Transactions on Dependable and Secure Computing, 2022, , 1-16.	3.7	1
196	Structural, thermal and electrical properties of plasma deposited a-C:F films. , 0, , .		0
197	Timing-driven MultiChip Module routing algorithm with crosstalk consideration. Journal of Electronics, 2006, 23, 741-744.	0.2	0
198	An Improved Heuristic Algorithm for MCM Substrate Test. , 2006, , .		0

#	ARTICLE	IF	CITATIONS
199	A novel ESD protection circuit applied in high-speed CMOS IC. , 2008, , .		0
200	First-principles study of boron doping-induced band gap narrowing in 3C-SiC. , 2009, , .		0
201	Strain coefficient measurement for the (100) uniaxial strain silicon by Raman spectroscopy. Science China Information Sciences, 2011, 54, 1762-1768.	2.7	0
202	Vertical-mesh-conscious-dynamic routing algorithm for fault tolerant 3D NoC. , 2016, , .		0
203	Influence of pulse parameters on the damage effect of the GaAs PHEMT caused by the repetition pulse. , 2016, , .		0
204	A first principle calculation of anisotropic elastic, mechanical and electronic properties of TiB. AIP Conference Proceedings, 2018, , .	0.3	0
205	H OEIN: A Hierarchical Hybrid Optical/Electrical Interconnection Network for Exascale Computing Systems. IEEE Transactions on Multi-Scale Computing Systems, 2018, 4, 722-733.	2.5	0
206	Interfacial electromagneticâ€“thermal characterization of a shielded pair through-silicon via a silicon interposer. Semiconductor Science and Technology, 2018, 33, 115022.	1.0	0
207	Dynamic determination method of spinning reserve capacity based on situation awareness of power systems. , 2019, , .		0
208	Numerical Modelling of Interconnect Electromigration Under Non-DC Stressing Conditions. IETE Journal of Research, 2020, 66, 85-90.	1.8	0
209	Design of a Si-based Lattice-matched GeSn/SiGeSn Multi-quantum-well Laser. Journal of Russian Laser Research, 2020, 41, 98-103.	0.3	0
210	Model for Rapidly Computing the Highest Temperature Based on Fermat Point in Chips. Journal of Thermophysics and Heat Transfer, 2021, 35, 92-97.	0.9	0
211	Fast-switching SOI-LIGBT with compound dielectric buried layer and assistant-depletion trench. Chinese Physics B, 2022, 31, 047304.	0.7	0
212	Intelligent optimization design of 2â€“2 piezo-composites for ultrasonic transducer. Sensors and Actuators A: Physical, 2021, 332, 113171.	2.0	0
213	Dynamic back-off chain-building scheme based on network state partition. Optical Engineering, 2020, 59, .	0.5	0
214	Balanced SIW BPF based on Through-Glass Vias. , 2020, , .		0
215	Novel low loss and snapback-free SOI LIGBT controlled by anode junction self-built potential. IEICE Electronics Express, 2022, 19, .	0.3	0
216	Novel Fast-switching LIGBT with Single-Step Low-k Dielectric Layer and Assistant-Depletion Trench. Silicon, 0, , 1.	1.8	0

#	ARTICLE	IF	CITATIONS
217	Novel anode Schottky trench contact controlled SOI LIGBT with low loss and snapback-free. IEICE Electronics Express, 2022, 19, 20220014-20220014.	0.3	0
218	Echo Signal Receiving and Data Conversion Integrated Circuits for Portable High-Frequency Ultrasonic Imaging System. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2022, 69, 1980-1993.	1.7	0
219	Two novel PSRR enhancement techniques for voltage reference of depletion NMOS. IEICE Electronics Express, 2022, , .	0.3	0